



**CHENMKO ENTERPRISE CO.,LTD**

*Lead free devices*

**SURFACE MOUNT  
High Voltage NPN Transistor**

**VOLTAGE 300 Volts CURRENT 500 mAmpere**

**CHTA42LPT**

**APPLICATION**

- \* Small Signal Amplifier .

**FEATURE**

- \* Surface mount package. (SOT-23)
- \* Low saturation voltage  $V_{CE(sat)}=0.5V$ (max.)( $I_C=20mA$ )
- \* Low cob. Cob=3.0pF(Typ.)
- \*  $P_D= 300mW$  (mounted on ceramic substrate).
- \* High saturation current capability.

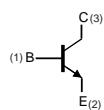
**CONSTRUCTION**

- \* NPN Silicon Transistor
- \* Epitaxial planner type

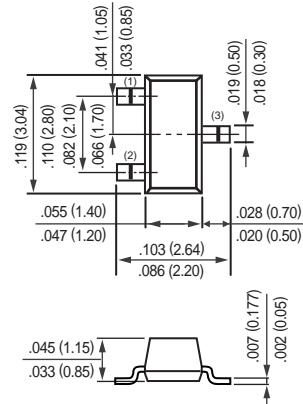
**MARKING**

- \* NB

**CIRCUIT**



**SOT-23**



Dimensions in inches and (millimeters)

**SOT-23**

**MAXIMUM RATINGS ( At  $T_A = 25^\circ C$  unless otherwise noted )**

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage	Open Emitter	$V_{CBO}$	-	300	Volts
Collector - Emitter Voltage	Open Base	$V_{CEO}$	-	300	Volts
Emitter - Base Voltage	Open Collector	$V_{EBO}$	-	6.0	Volts
Collector Current DC		$I_C$	-	500	mAmps
Peak Collector Current		$I_{CM}$	-	500	mAmps
Peak Base Current		$I_{BM}$	-	15	mAmps
Total Power Dissipation	$T_A \leq 25^\circ C$ ; Note 1	$P_{TOT}$	-	300	mW
Storage Temperature		$T_{STG}$	-55	+150	°C
Junction Temperature		$T_J$	-	+150	°C
Operating Ambient Temperature		$T_{AMB}$	-55	+150	°C

**Note**

1. Transistor mounted on ceramic substrate 50mmX50mmx0.8t.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

## RATING CHARACTERISTICS ( CHTA42LPT )

ELECTRICAL CHARACTERISTICS ( At TA = 25°C unless otherwise noted )

PARAMETERS	CONDITION	SYMBOL	MIN.	TYPE	MAX.	UNITS
Collector Cut-off Current	I <sub>E</sub> =0; V <sub>CB</sub> =200V	I <sub>CBO</sub>	-	-	0.1	uA
Emitter Cut-off Current	I <sub>C</sub> =0; V <sub>BE</sub> =6.0V	I <sub>EBO</sub>	-	-	0.1	uA
DC Current Gain	V <sub>CE</sub> =10V; Note 1 I <sub>C</sub> =1.0mA I <sub>C</sub> =10mA I <sub>C</sub> =30mA	$\text{h}_{FE}$	25 40 40	- - -	- - -	
Collector-Emitter Saturation Voltage	I <sub>C</sub> =20mA; I <sub>B</sub> =2mA	V <sub>CE(sat)</sub>	-	-	0.5	Volts
Base-Emitter Saturatio Voltage	I <sub>C</sub> =20mA; I <sub>B</sub> =2mA	V <sub>BE(sat)</sub>	-	-	0.9	Volts
Output Collector Capacitance	I <sub>E</sub> =I <sub>B</sub> =0; V <sub>CB</sub> =20V; f=1MHz	C <sub>ob</sub>	-	-	3.0	pF
Transition Frequency	I <sub>C</sub> =10mA; V <sub>CE</sub> =20V; f=100MHz	f <sub>T</sub>	50	-	-	MHz

**Note :**

- Pulse test: tp ≤ 300uSec; δ ≤ 0.02.

## RATING CHARACTERISTIC CURVES ( CHTA42LPT )

Figure 1. DC Current Gain

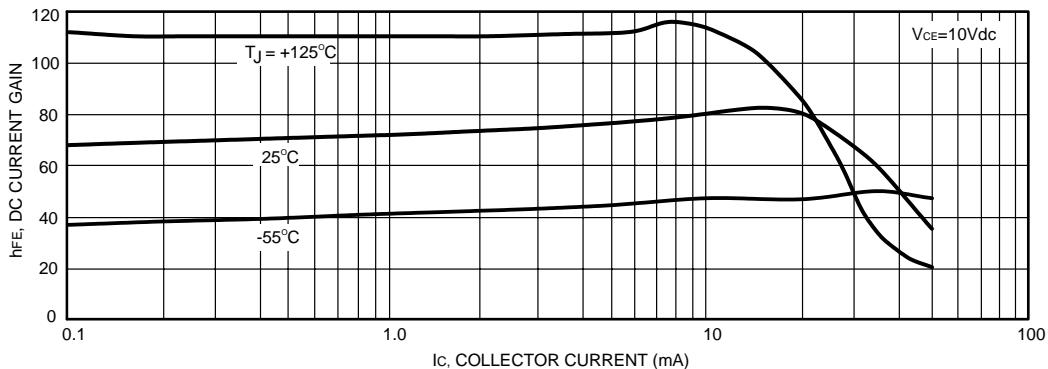


Figure 2. Capacitance

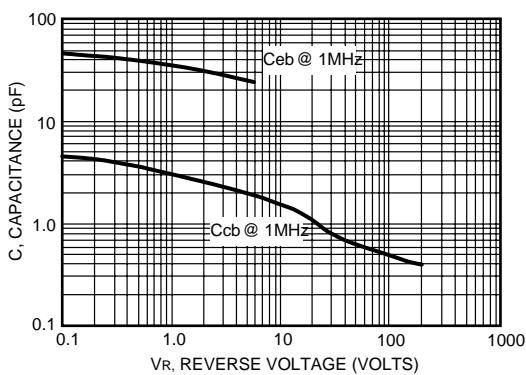


Figure 3. Current-Gain - Bandwidth

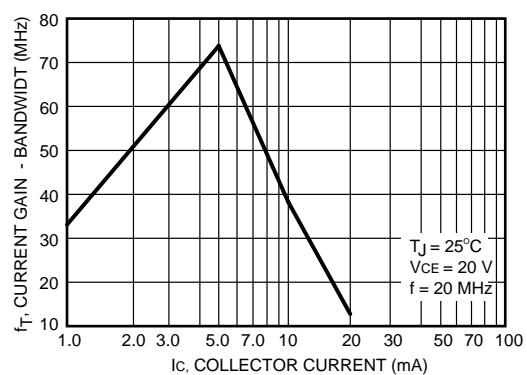


Figure 4. "ON" Voltages

